

Title (en)

CRYSTALLISATION OF AMORPHOUS SILICON FROM A SILICON-RICH ALUMINIUM SUBSTRATE

Title (de)

KRISTALLISATION VON AMORPHEM SILICIUM AUS EINEM SILICIUMREICHEN ALUMINIUMSUBSTRAT

Title (fr)

CRISTALLISATION DE SILICIUM AMORPHE À PARTIR D'UN SUBSTRAT D'ALUMINIUM RICHE EN SILICIUM

Publication

**EP 3449044 A1 20190306 (FR)**

Application

**EP 17723452 A 20170421**

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- FR 2017050951 W 20170421

Abstract (en)

[origin: WO2017187061A1] The invention relates to a method for manufacturing a semiconductor component including a thin layer of crystalline silicon on a substrate, which includes the following steps: providing a silicon-rich aluminium substrate (S0); depositing a thin layer of amorphous silicon on said substrate (S1); and applying thermal annealing (S2) to said thin layer of amorphous silicon in order to obtain a thin layer of crystalline silicon on said substrate.

IPC 8 full level

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Citation (search report)

See references of WO 2017187061A1

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